Tianyi Han

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/11176269/publications.pdf

Version: 2024-02-01

		516710	580821
25	1,542	16	25
papers	citations	h-index	g-index
25	25	25	2252
25	25	25	3352
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Spectroscopy signatures of electron correlations in a trilayer graphene/hBN moiré superlattice. Science, 2022, 375, 1295-1299.	12.6	30
2	Bridging the gap between atomically thin semiconductors and metal leads. Nature Communications, 2022, 13, 1777.	12.8	17
3	A Tunable Resonant Circuit Based on Graphene Quantum Capacitor. Advanced Electronic Materials, 2021, 7, 2001009.	5.1	1
4	Accurate Measurement of the Gap of <mml:math display="inline" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mrow><mml:mi>Graphene</mml:mi><mml:mo>/</mml:mo><mml:mi>h<td>nml728i><td>nml:onrow><m< td=""></m<></td></td></mml:mi></mml:mrow></mml:mrow></mml:math>	nml 7 28i> <td>nml:onrow><m< td=""></m<></td>	nm l:o nrow> <m< td=""></m<>
5	Intrinsic valley Hall transport in atomically thin MoS2. Nature Communications, 2019, 10, 611.	12.8	77
6	Determining Interaction Enhanced Valley Susceptibility in Spin-Valley-Locked MoS ₂ . Nano Letters, 2019, 19, 1736-1742.	9.1	35
7	Gate-tunable strong-weak localization transition in few-layer black phosphorus. Nanotechnology, 2018, 29, 035204.	2.6	10
8	Fluctuation-induced tunneling conduction in iodine-doped bilayer graphene. Journal of Applied Physics, 2018, 123, 244302.	2.5	2
9	xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"> <mml:mi>p</mml:mi> -Type Few-Layer <mml:math display="inline" xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mrow><mml:mi>WSe</mml:mi></mml:mrow><mml:mn>2<td>7.8 nml:mn><!--</td--><td>37 mml:msub></td></td></mml:mn></mml:msub></mml:mrow></mml:math>	7. 8 nml:mn> </td <td>37 mml:msub></td>	37 mml:msub>
10	Physical Review Letters, 2017, 118, 067702. Isolation and Characterization of Few-Layer Manganese Thiophosphite. ACS Nano, 2017, 11, 11330-11336.	14.6	98
11	Ambipolar quantum transport in few-layer black phosphorus. Physical Review B, 2017, 96, .	3.2	26
12	Achieving Ultrahigh Carrier Mobility in Two-Dimensional Hole Gas of Black Phosphorus. Nano Letters, 2016, 16, 7768-7773.	9.1	242
13	Charge density wave phase transition on the surface of electrostatically doped multilayer graphene. Applied Physics Letters, 2016, 109, .	3.3	4
14	Probing the electronic states and impurity effects in black phosphorus vertical heterostructures. 2D Materials, 2016, 3, 015012.	4.4	16
15	Negative compressibility in graphene-terminated black phosphorus heterostructures. Physical Review B, 2016, 93, .	3.2	10
16	Even–odd layer-dependent magnetotransport of high-mobility Q-valley electrons in transition metal disulfides. Nature Communications, 2016, 7, 12955.	12.8	82
17	Universal low-temperature Ohmic contacts for quantum transport in transition metal dichalcogenides. 2D Materials, 2016, 3, 021007.	4.4	102
18	Type-controlled nanodevices based on encapsulated few-layer black phosphorus for quantum transport. 2D Materials, 2016, 3, 031001.	4.4	19

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#	Article	IF	CITATION
19	A fast transfer-free synthesis of high-quality monolayer graphene on insulating substrates by a simple rapid thermal treatment. Nanoscale, 2016, 8, 2594-2600.	5.6	20
20	Detection of interlayer interaction in few-layer graphene. Physical Review B, 2015, 92, .	3.2	22
21	Probing the electron states and metal-insulator transition mechanisms in molybdenum disulphide vertical heterostructures. Nature Communications, 2015, 6, 6088.	12.8	181
22	Probing Defectâ€Induced Midgap States in MoS ₂ Through Graphene–MoS ₂ Heterostructures. Advanced Materials Interfaces, 2015, 2, 1500064.	3.7	17
23	van der Waals Epitaxial Growth of Atomically Thin Bi ₂ Se ₃ and Thickness-Dependent Topological Phase Transition. Nano Letters, 2015, 15, 2645-2651.	9.1	54
24	High-quality sandwiched black phosphorus heterostructure and its quantum oscillations. Nature Communications, 2015, 6, 7315.	12.8	423
25	Side-gate modulation effects on high-quality BN-Graphene-BN nanoribbon capacitors. Applied Physics Letters, 2014, 105, .	3.3	7